

Monday, September 28, 2026									
Start	End	Duration	Session	Number	Speaker	Organization	Country	Title	Chairs
08:45	09:00	00:15	Opening Remarks						
09:00	09:45	00:45	Keynote 1	KN1	Maud Vinet	Quobly	France	Building industrial-scale quantum computing on silicon	
09:45	10:15	00:30	S1 - Quantum	S1-INV1	Mathilde Lemang	Qphox	The Netherlands	Design and process development of integrated quantum transducers for scalable quantum systems	
10:15	10:35	00:20		S1-01	François Lefloch	CEA IRIG	France	Low temperature properties of CoSi ₂ based superconducting transistors	
10:35	10:55	00:20	Coffee Break						
10:55	11:15	00:20	S2 - Contact 1	S2 - 01	Osamu Nakatsuka	Nagoya University	Japan	Ultra-low Schottky barrier height in epitaxial-CaGe ₂ /n-Ge(111) contact: What is the key to lowering SBH of germanide/n-Ge contact?	
11:15	11:35	00:20		S2 - 02	Marie Merlin	CEA-Leti	France	Insights into Early Phase Formation in Ti-Based Contacts for Advanced FD-SOI	
11:35	11:55	00:20		S2 - 03	Jonas Müller	LAAS-CNRS	France	Engineering of nano-scale contacts for 3D silicon devices through geometrical confinement of binary and ternary nickel silicide alloys	
11:55	13:30	01:35	Lunch Break						
13:30	13:45	00:15	S3 - Special Session	S3 - 01	Inge Asselberghs	imec	Belgium	NanoC Pilot Line	
13:45	14:00	00:15		S3 - 02	Dominique Noguet	CEA-Leti	France	FAMES Pilot Line	
14:00	14:15	00:15	Short Break						
14:15	14:45	00:30	S4 - Annealing 1	S4 - INV1	Ray Duffy	Tyndall National Institute / University College Cork	Ireland	Doping solutions through recrystallisation of amorphous semiconductors; issues and challenges for planar CMOS, thin-body devices, and thin-film materials	
14:45	15:05	00:20		S4 - 01	Taiga Fuse	Institute of Science Tokyo	Japan	Edge-Contacted PVD-ZrS ₂ Field Effect Transistor with Reduced Thermal Budget by H ₂ S Annealing	
15:05	15:25	00:20		S4 - 02	Yuanning Chen	MicroSol Technologies Inc.	USA	High-Fractional Dopant Activation in Ultra-Shallow Junction Semiconductor Devices via Low-Temperature Plasma-Enhanced Annealing	
15:25	15:45	00:20		S4 - 03	Anthony Albanese	Sumitomo (SHI) Material Solutions Europe	France	Polycrystalline silicon grain size tuning and dopant activation by laser annealing	
15:45	16:05	00:20	Coffee Break						
16:05	16:35	00:30	S5 - Power devices	S5 - INV1	TaeGi Lee	Asahi Kasei Corp. / Nagoya University	Japan	MOVPE-Grown Pseudomorphic AlN/GaN/AlN HEMTs on AlN Substrates Enabling High Breakdown Field and Collapse-Free Operation	
16:35	17:05	00:30		S5 - INV2	Jan Prominski	Axcelis Technologies	Germany	Enabling SiC Superjunction Power Devices by Ultra-High-Energy Ion Implantation	
17:05	17:20	00:15	S6 - Poster Session Teasing	Each poster presenter is allotted two minutes for their introduction, which should be presented on a single slide					
17:20	18:00	00:40	S6 - Poster Session						
19:00	21:00	02:00	Conference Dinner						

Tuesday, September 29, 2026								
Start	End	Duration	Session	Number	Speaker	Organization	Country	Title
08:45	09:00	00:15	Opening Remarks					
09:00	09:45	00:45	Keynote 2	KN2	Nicolas Breil	Applied Materials	USA	Epitaxy process solutions for AI computing applications
09:45	10:15	00:30	S7 - Epitaxy	S7-INV1	Rami Khazaka	ASM	Belgium	Enabling Future Technology Nodes Through Ultra Low Temperature Epitaxy
10:15	10:35	00:20		S7-01	Thomas Dursap	imec	Belgium	Low temperature selective Si:P epitaxy development for NMOS applications
10:35	10:55	00:20	Coffee Break					
10:55	11:25	00:30	S8 - Characterization	S8 - INV1	Claudia Fleischmann	imec / KU Leuven	Belgium	From Material Insights to Device Scaling: Grand Challenges and Emerging Solutions in Characterization, Metrology and Inspection
11:25	11:45	00:20		S8 - 01	Yuta Okuyama	University of Tsukuba	Japan	Bandgap Evaluation of Si-Doped α -(AlGa) ₂ O ₃ by XPS
11:45	13:30	01:45	Lunch Break (including Committee Meeting)					
13:30	14:00	00:30	S9 - Annealing 2	S9 - INV1	Louis Thuries	Sumitomo (SHI) Material Solutions Europe	France	How Advanced Laser Annealing Technology Enables AI Performance at Scale
14:00	14:20	00:20		S9 - 01	Taehan Kim	Nagoya University	Japan	Recrystallization of Ion-Implanted High-Sn-Composition Ge _{1-x} Sn _x Layers by Pulsed Laser Annealing
14:20	14:40	00:20		S9 - 02	Gabin Ternin-Rozat	CEA-Leti	France	Advanced materials calibration for nanosecond laser annealing simulations
14:40	14:55	00:15	Short Break					
14:55	15:25	00:30	S10 - Contact 2	S10 - INV1	Frank Torregrosa	Ion Beam Services	France	30 years development of Plasma Immersion Ion Implantation technology and process at IBS on PULSion® Equipment : advantages and challenges for various applications including memories, logic, image sensors and power devices
15:25	15:45	00:20		S10 - 01	Esteban Marques	SCREEN-SPE	The Netherlands	Temperature and Chemical Dependence of Titanium Nitride Wet Etching Using Ammonia Peroxide Mixture for Advanced CMOS Junction Integration
15:45	16:05	00:20		S10 - 02	Ali Ahmad	CEA-Leti	France	Ni-Based Ohmic Contacts on p-GaAsSb / InP: Interfacial alloying & Electrical Properties
16:05	16:25	00:20		S10 - 03	Dominique Mangelinck	CNRS IM2NP	France	Agglomeration of Ni(Pt)Si thin films: role of Pt
16:25	16:45	00:20	Coffee Break					
16:45	17:15	00:30	S11 - Advanced Devices	S11 - INV1	Frédéric Boeuf	STMicroelectronics	France	Silicon Photonics: A Technology for AI-Datacenter Applications and Beyond
17:15	17:45	00:30		S11 - INV2	Khaled Driche	DiamFab	France	Diamond as an Ultra Wide Bandgap Semiconductor: Challenges and Future Perspectives
17:45	18:00	00:15	Closing Remarks and Award Ceremony					